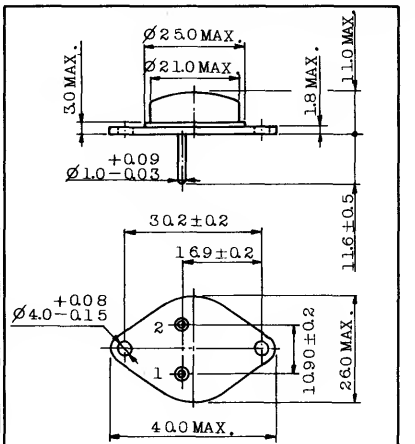
SILICON NPN TRIPLE DIFFUSED TYPE
(DARLINGTON POWER)

2SD1460

HIGH CURRENT SWITCHING APPLICATIONS.

FEATURES:
- High Collector Current : I_C=30A
- High DC Current Gain : h_{FE}=1000(Min.)(V_{CE}=5V, I_C=20A)
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor.

Unit in mm



1. BASE
2. EMITTER
COLLECTOR (CASE)

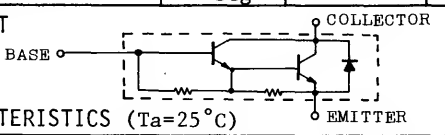
JEDEC	TO-3
EIAJ	TC-3, TB-3
TOSHIBA	2-21A1A

Mounting Kit No. AC73
Weight : 13g

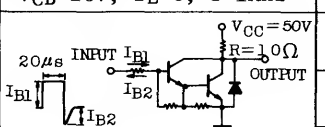
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	A
Base Current	I_B	5	A
Collector Power Dissipation (Tc=25°C)	P_C	200	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−65 ~ 150	°C

EQUIVALENT CIRCUIT

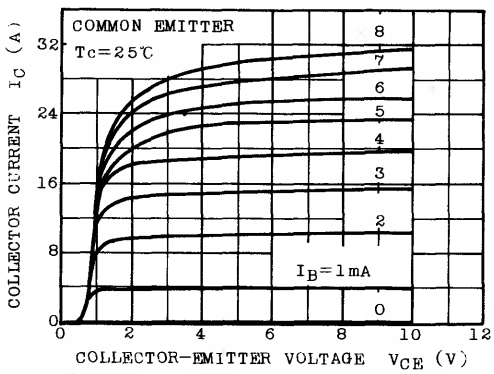


ELECTRICAL CHARACTERISTICS (Ta=25°C)

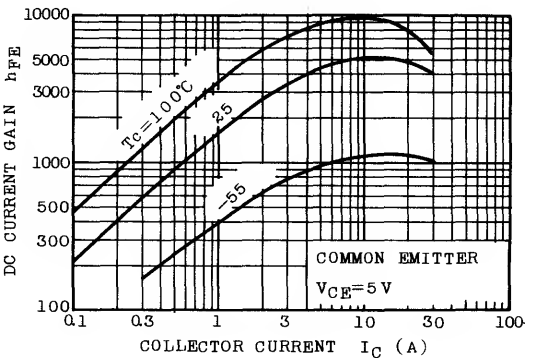
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB}=100V, I_E=0	−	−	100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB}=5V, I_C=0	−	−	10	mA
Collector-Emitter Breakdwon Voltage		$V_{(BR)CEO}$	I_C=50mA, I_B=0	100	−	−	V
DC Current Gain		$h_{FE(1)}$	V_{CE}=5V, I_C=20A	1000	−	−	
		$h_{FE(2)}$	V_{CE}=5V, I_C=30A	200	−	−	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=20A, I_B=0.2A	−	−	1.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$		−	−	2.0	V
Emitter-Collector Forward Voltage		V_{ECF}	I_E=10A, I_B=0	−	−	3	V
Transition Frequency		f_T	V_{CE}=5V, I_C=1A	−	10	−	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	−	500	−	pF
Switching Time	Turn on Time	t_{on}		−	1.5	−	μs
	Storage Time	t_{stg}		−	10	−	
	Fall Time	t_f		−	1.5	−	

I_{B1}=−I_{B2}=0.01A
DUTY CYCLE≦1%

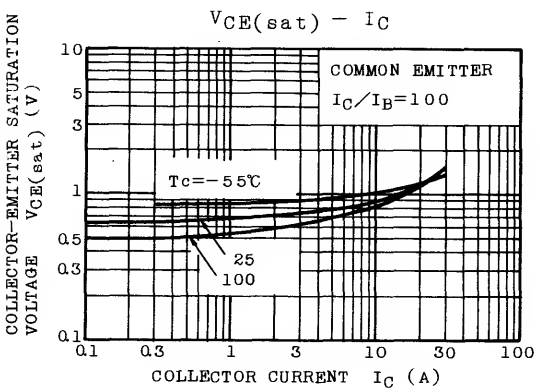
$I_C - V_{CE}$



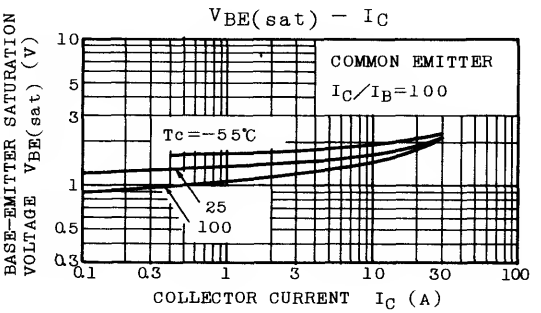
$h_{FE} - I_C$



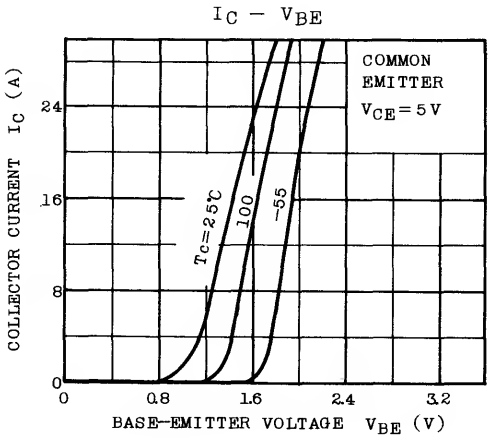
$V_{CE(sat)} - I_C$



$V_{BE(sat)} - I_C$



$I_C - V_{BE}$



SAFE OPERATING AREA